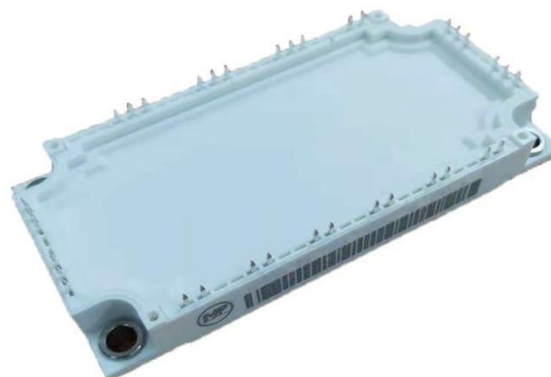


Electrical Features

- Trench/Fieldstop IGBT
- V_{CEsat} with positive Temperature Coefficient
- Low V_{CEsat}

Typical Applications

- Auxiliary inverters
- Motor drives
- Servo drives



Mechanical Features

- High power density
- Integrated NTC temperature sensor
- Copper base plate
- Solder contact technology
- Standard housing

IGBT, Inverter

Maximum Rated Values							
Symbol	Item	Conditions	Rating	Unit			
IGBT							
V_{CES}	Collector-emitter voltage	$T_{vj}=25^{\circ}C$	1200	V			
V_{GES}	Gate-emitter voltage	-	± 20	V			
I_C	Collector current,DC	$T_C=100^{\circ}C, T_{vj}=175^{\circ}C$	150	A			
I_{CRM}	Repetitive peak collector current	$t_p=1ms$	300	A			
P_{tot}	Total power dissipation	$T_C=25^{\circ}C, T_{vj}=175^{\circ}C$	750	W			
Characteristics Values							
Symbol	Item	Conditions	Values			Unit	
			Min.	Typ.	Max.		
I_{CES}	Collector-emitter cut-off current	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$	-	-	1	mA	
I_{GES}	Gate leakage current	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$	-	-	100	nA	
$V_{GE(th)}$	Gate-emitter threshold voltage	$I_C=5.7mA, V_{CE}=V_{GE}, T_{vj}=25^{\circ}C$	5.2	5.79	6.2	V	
V_{CEsat}	Collector-emitter saturation voltage	$I_C=150A$ $V_{GE}=15V$	$T_{vj}=25^{\circ}C$	-	1.92	2.5	V
			$T_{vj}=125^{\circ}C$	-	2.34	-	
			$T_{vj}=150^{\circ}C$	-	2.43	-	
C_{ies}	Input capacitance	$V_{CE}=25V, V_{GE}=0V$	-	10.6	-	nF	
C_{res}	Reverse transfer capacitance	$f=1MHz, T_{vj}=25^{\circ}C$	-	0.36	-		
Q_G	Gate charge	$V_{CC}=600V, I_C=150A$ $V_{GE}=-15...+15V, T_{vj}=25^{\circ}C$	-	0.939	-	μC	
R_g	Internal gate resistance	$T_{vj}=25^{\circ}C$	-	1.2	-	Ω	

t _{d(on)}	Turn-on delay time	V _{CC} =600V I _C =150A V _{GE} =±15V R _{G(on)} =3.9Ω R _{G(off)} =3.9Ω	T _{vj} =25°C	-	14.6	-	ns		
			T _{vj} =125°C	-	18.6	-			
			T _{vj} =150°C	-	20.5	-			
T _{vj} =25°C	-		51.5	-					
T _{vj} =125°C	-		53.3	-					
T _{vj} =150°C	-		54.5	-					
T _{vj} =25°C	-		277.7	-					
T _{vj} =125°C	-		310.6	-					
T _{vj} =150°C	-		361.3	-					
T _{vj} =25°C	-		161.3	-					
t _r	Rise time	V _{CC} =600V, I _C =150A V _{GE} =±15V R _{G(on)} =3.9Ω R _{G(off)} =3.9Ω	T _{vj} =25°C	-	12.4	-	mJ		
E _{on}	Turn-on energy (per pulse)		T _{vj} =125°C	-	19.1	-			
			T _{vj} =150°C	-	21.5	-			
			T _{vj} =25°C	-	9.3	-			
E _{off}	Turn-off energy (per pulse)		T _{vj} =125°C	-	12.5	-			
			T _{vj} =150°C	-	13.4	-			
			T _{vj} =150°C	-	13.4	-			
t _f	Fall time		V _{CC} =600V, I _C =150A V _{GE} =±15V, R _{G(off)} =3.9Ω du/dt=5787V/μs(T _{vj} =150°C)	T _{vj} =25°C	-	9.3		-	mJ
E _{on}	Turn-on energy (per pulse)			T _{vj} =125°C	-	12.5		-	
				T _{vj} =150°C	-	13.4		-	
		T _{vj} =150°C		-	13.4	-			
E _{off}	Turn-off energy (per pulse)	T _{vj} =25°C		-	9.3	-			
		T _{vj} =125°C		-	12.5	-			
		T _{vj} =150°C		-	13.4	-			
SC data	Short-circuit current	V _{CC} =600V, V _{GE} ≤15V, T _{vj} =25°C V _{CES} ≤1200V, t _p ≤10μs		-	-	1230	-	A	
				-	-	1230	-		
				-	-	1230	-		
R _{thJC}	Thermal resistance, junction to case		Per IGBT	-	-	0.2	K/W		
R _{thCH}	Thermal resistance, case to heatsink		Per IGBT, λgrease=1W/(m·K)	-	0.082	-	K/W		
T _{vjop}	Temperature under switching conditions			-40		150	°C		
Diode, Inverter									
Maximum Rated Values									
Symbol	Item		Conditions				Rating		Unit
V _{RRM}	Repetitive peak reverse voltage		T _{vj} =25°C				1200		V
I _F	Forward current, DC					150	A		
I _{FRM}	Repetitive peak forward current	t _p =1ms				300	A		
I ² t	I ² t-value	V _R =0V, t _p =10ms, T _{vj} =150°C				2950	A ² s		
Characteristic Values									
V _F	Continuous forward voltage	I _F =150A V _{GE} =0V	T _{vj} =25°C	-	2.02	2.5	V		
			T _{vj} =125°C	-	1.81	-			
			T _{vj} =150°C	-	1.76	-			
I _{RM}	Peak reverse recovery current		V _R =600V I _F =150A V _{GE} =-15V -di _F /dt=3810A/μs (T _{vj} =150°C)	T _{vj} =25°C	-	152	-	A	
				T _{vj} =125°C	-	202	-		
				T _{vj} =150°C	-	223	-		
t _{rr}	Reverse recovery time			V _R =600V I _F =150A V _{GE} =-15V -di _F /dt=3810A/μs (T _{vj} =150°C)	T _{vj} =25°C	-	89.8	-	ns
					T _{vj} =125°C	-	169.5	-	
					T _{vj} =150°C	-	193.8	-	
Q _r	Recovered charge				V _R =600V I _F =150A V _{GE} =-15V -di _F /dt=3810A/μs (T _{vj} =150°C)	T _{vj} =25°C	-	7.59	-
		T _{vj} =125°C				-	27.26	-	
		T _{vj} =150°C				-	33.22	-	

E _{rec}	Reverse recovery energy		T _{vj} =25°C	-	4.20	-	mJ
			T _{vj} =125°C	-	11.16	-	
			T _{vj} =150°C	-	13.93	-	
R _{thJC}	Thermal resistance, junction to case	per diode	-	-	0.375	K/W	
R _{thCH}	Thermal resistance, case to heatsink	per diode, λ _{grease} =1 W/(m • K)	-	0.155	-	K/W	
T _{vjop}	Temperature under switching conditions		-40		150	°C	

Note:

IGBT electrical characteristics according to IEC 60747 – 9

Diode electrical characteristics according to IEC 60747 – 2

NTC Thermistor Characteristics

Symbol	Item	Conditions	Values			Unit
			Min.	Typ.	Max.	
R ₂₅	Rated resistance	T _C =25°C	-	5	-	kΩ
ΔR/R	Deviation of resistance	T _C =100°C, R ₁₀₀ =493Ω	-5	-	5	%
P ₂₅	Power dissipation	T _C =25°C	-	-	20	mW
B _{25/50}	B-constant	R ₂ =R ₂₅ exp[B _{25/50} (1/T ₂ -1/(298.15K))]	-	3375	-	K
B _{25/80}	B-constant	R ₂ =R ₂₅ exp[B _{25/80} (1/T ₂ -1/(298.15K))]	-	3411	-	
B _{25/100}	B-constant	R ₂ =R ₂₅ exp[B _{25/100} (1/T ₂ -1/(298.15K))]	-	3433	-	

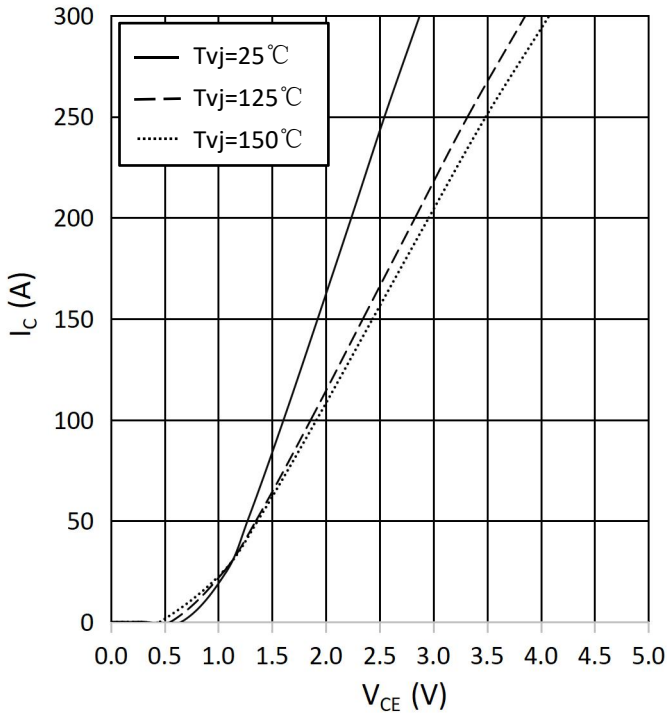
Module

Symbol	Item	Conditions	Rating			Unit
			Min.	Typ.	Max.	
V _{ISOL}	Isolation voltage	Terminals to baseplate, RMS, f=50Hz, t=1min	2500			V
T _{vjmax}	Maximum junction temperature	-	175			°C
T _{vjop}	Operating junction temperature	Continuous operationg(underswitching)	-40~150			°C
T _{stg}	Storage temperature	-	-40~125			°C
Symbol	Item	Conditions	Values			Unit
			Min.	Typ.	Max.	
M	Mounting torque for modul mounting	-	3	-	6	Nm
ds	Creepage distance	Terminal to terminal	-	-	-	mm
		Terminal to base plate	-	10	-	
da	Clearance	Terminal to terminal	-	-	-	mm
		Terminal to base plate	-	7.5	-	
m	Weight	-	-	290	-	g

output characteristic IGBT,Inverter (typical)

$I_C = f(V_{CE})$

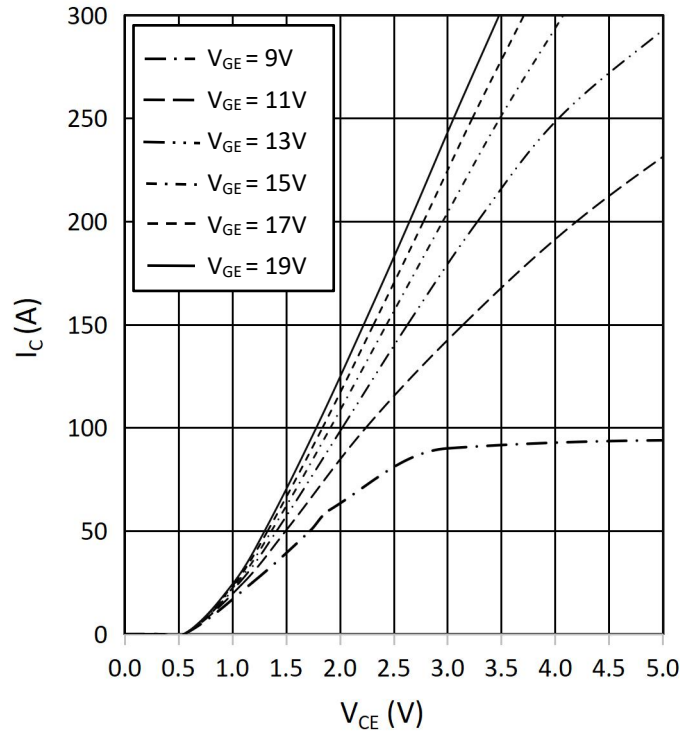
$V_{GE} = 15V$



output characteristic IGBT,Inverter (typical)

$I_C = f(V_{CE})$

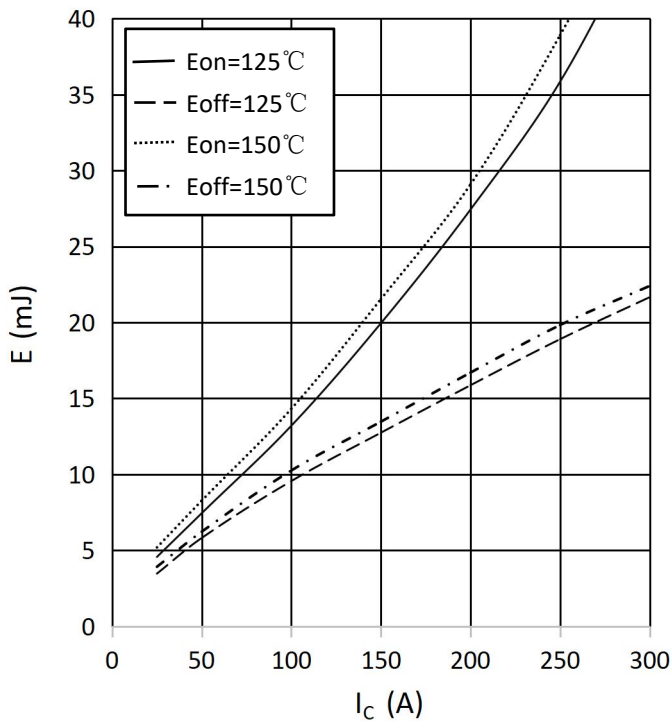
$T_{vj} = 150^{\circ}C$



switching losses IGBT,Inverter (typical)

$E_{on} = f(I_C), E_{off} = f(I_C)$

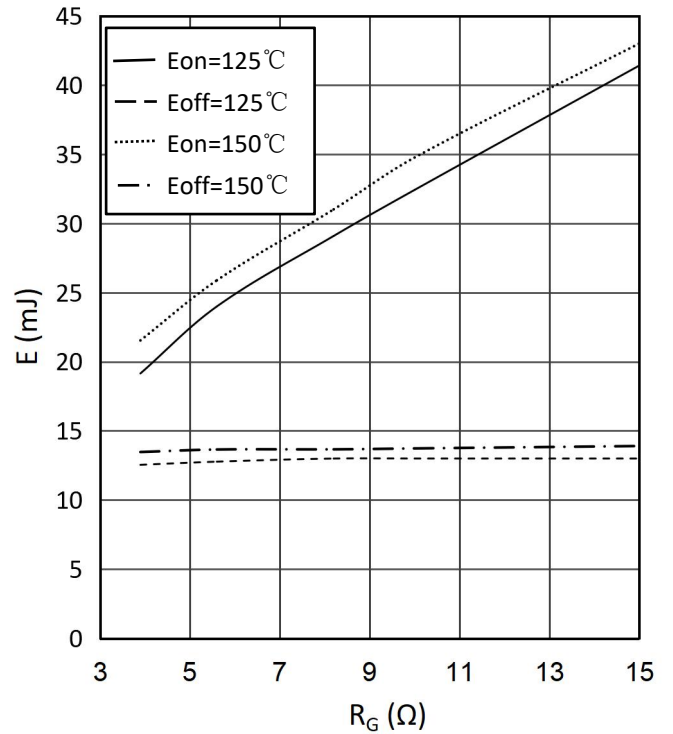
$V_{GE} = \pm 15V, R_{Gon} = 3.9\Omega, R_{Goff} = 3.9\Omega, V_{CE} = 600V$



switching losses IGBT,Inverter (typical)

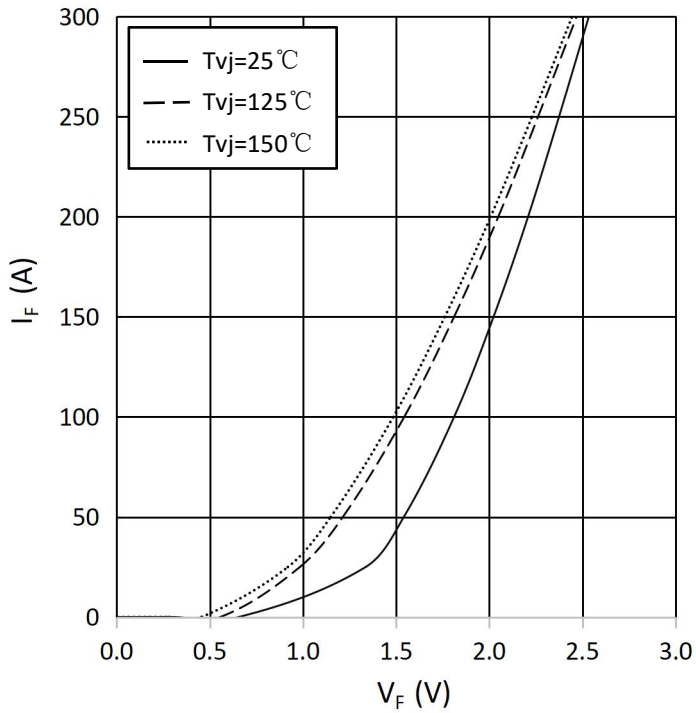
$E_{on} = f(R_G), E_{off} = f(R_G)$

$V_{GE} = \pm 15V, I_C = 150A, V_{CE} = 600V$



forward characteristic of Diode, Inverter (typical)

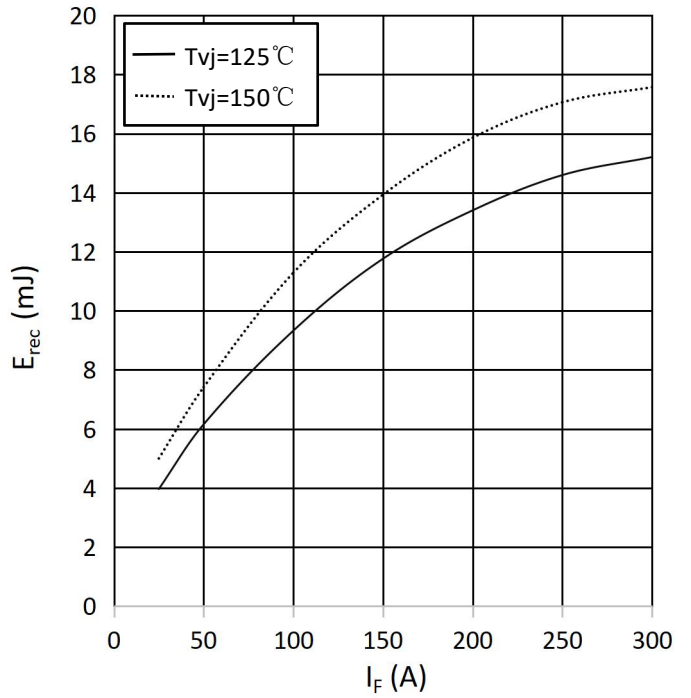
$I_F = f(V_F)$



switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$

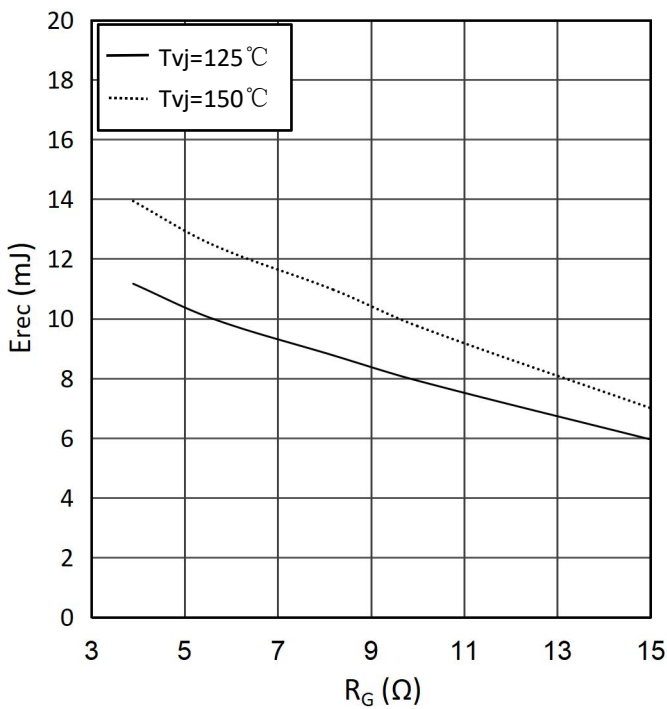
$R_{Gon} = 3.9\Omega, V_{CE} = 600\text{ V}$



switching losses Diode, Inverter (typical)

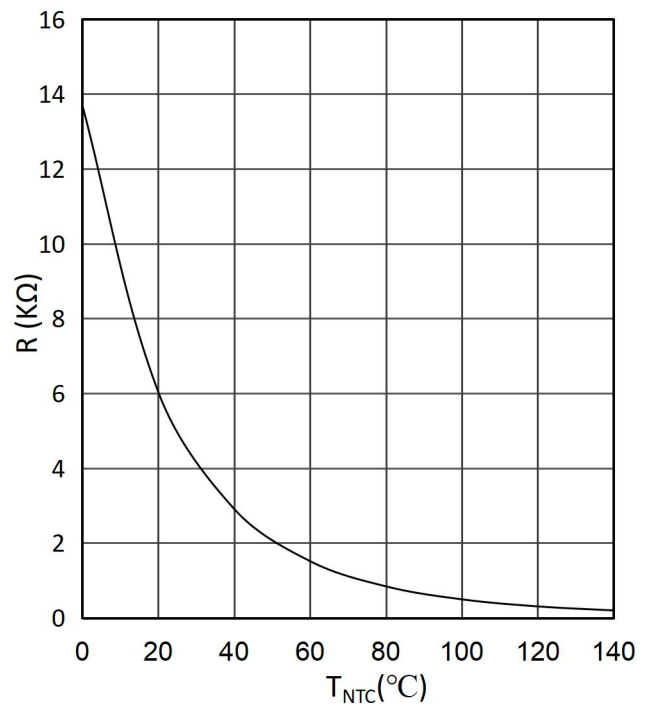
$E_{rec} = f(R_G)$

$I_F = 150\text{A}, V_{CE} = 600\text{V}$

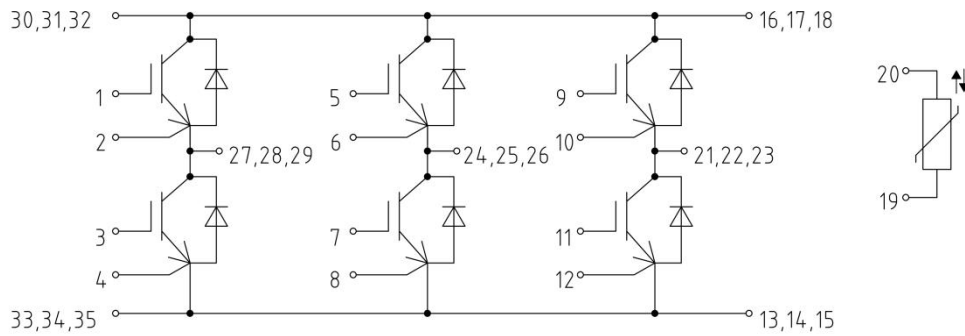


NTC-Thermistor-temperature characteristic(typical)

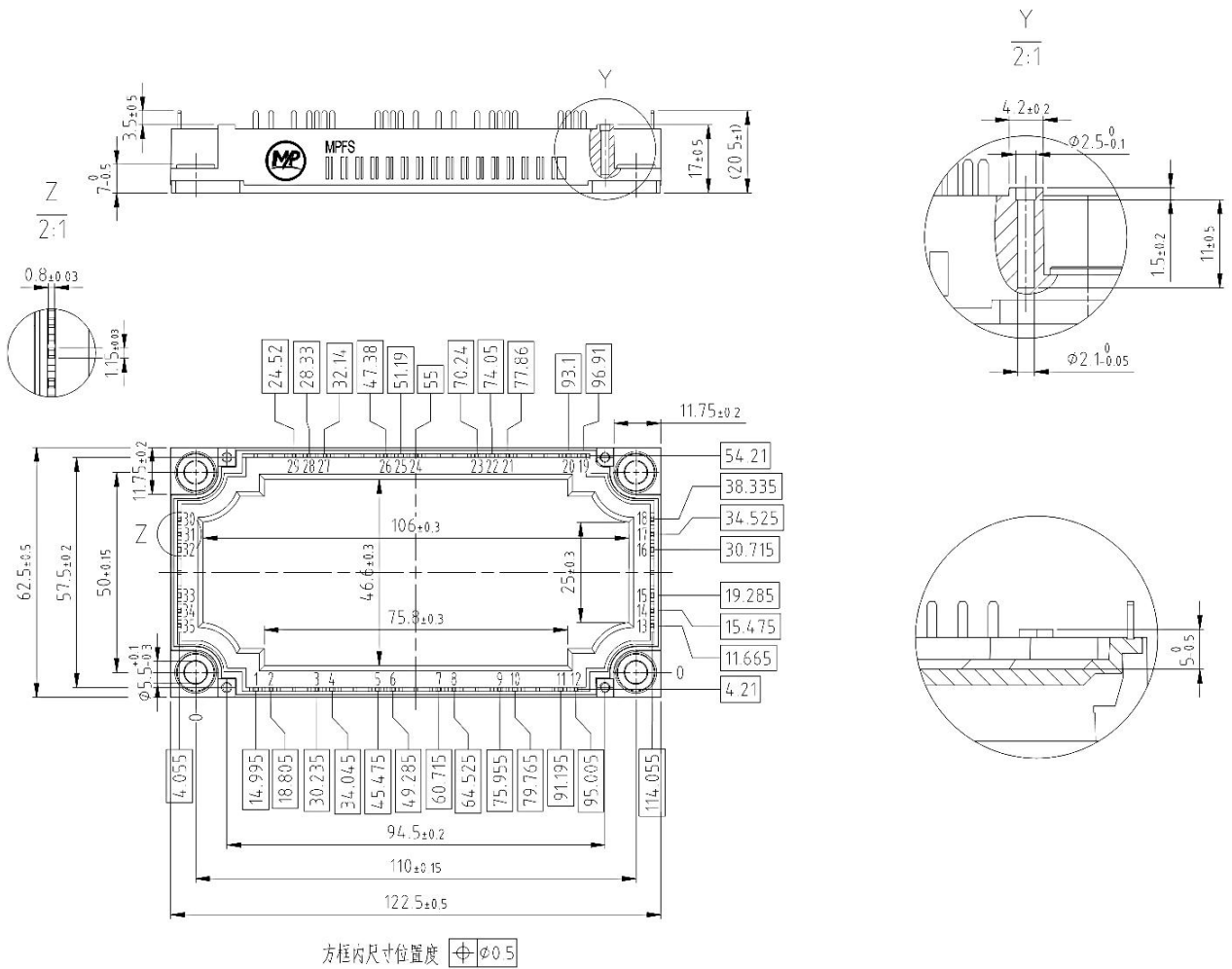
$R=f(T)$



Circuit Diagram



Package Outlines



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